

L Number	Hits	Search Text	DB	Time stamp
-	146	(423/346).CCLS.	USPAT; US-PGPUB	2003/11/03 11:50
-	551	(423/345,346).CCLS.	USPAT; US-PGPUB	2003/11/03 11:51
-	20	((423/346).CCLS.) and conductivity	USPAT; US-PGPUB	2003/11/03 11:51
-	4	((423/346).CCLS.) and conductivity with (w or mk or "w/mk")	USPAT; US-PGPUB	2003/11/03 11:55
-	4	((423/346).CCLS.) and conductivity) and . conductivity with (w or mk or "w/mk")	USPAT; US-PGPUB	2003/11/03 12:02
-	629	((silicon adj carbide) or sic) same (conductivity with (w or mk or "w/mk"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/03 12:03
-	198	((silicon adj carbide) or sic) same (conductivity with (w or mk or "w/mk"))) and (cvd or (chemical adj vapor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/03 13:09
-	62	(cvd or (chemical adj vapor)) same ((silicon adj carbide) or sic) same (conductivity with (w or mk or "w/mk"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/03 12:06
-	62	(cvd or (chemical adj vapor)) same ((silicon adj carbide) or sic) same (conductivity with (kw or w or mk or "w/mk"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/03 12:07
-	62	(cvd or (chemical adj vapor)) same ((silicon adj carbide) or sic) same (conductivity with (kw or w or mk or "w/mk" or "kw/mk"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/03 13:14
-	198	(cvd or (chemical adj vapor)) and ((silicon adj carbide) or sic) same (conductivity with (kw or w or mk or "w/mk" or "kw/mk"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/03 13:04
-	9	((cvd or (chemical adj vapor)) and ((silicon adj carbide) or sic) same (conductivity with (kw or w or mk or "w/mk" or "kw/mk"))) and polycrystalline with phase	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/03 12:16
-	54	((cvd or (chemical adj vapor)) and ((silicon adj carbide) or sic) same (conductivity with (kw or w or mk or "w/mk" or "kw/mk"))) and (beta or ".beta.sic" or ".beta."\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/03 12:17
-	198	(cvd or (chemical adj vapor)) and ((silicon adj carbide) or sic) same (conductivity with (kw or w or mk or "w/mk" or "kw/mk"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/03 13:09
-	8	((cvd or (chemical adj vapor)) and ((silicon adj carbide) or sic) same (conductivity with (kw or w or mk or "w/mk" or "kw/mk"))) and order with ratio	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/03 13:08
-	3	((cvd or (chemical adj vapor)) and ((silicon adj carbide) or sic) same (conductivity with (kw or w or mk or "w/mk" or "kw/mk"))) and crystalline with ratio	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/03 13:08
-	7	((cvd or (chemical adj vapor)) and ((silicon adj carbide) or sic) same (conductivity with (kw or w or mk or "w/mk" or "kw/mk"))) and crystalline with order	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/03 13:08

-	1	(cvd or (chemical adj vapor)) and ((silicon adj carbide) or sic) same (\$4crystalline with (order adj ratio))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/03 13:13
-	1	(cvd or (chemical adj vapor)) and ((silicon adj carbide) or sic) same (order adj ratio))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/03 13:11
-	1	(cvd or (chemical adj vapor)) and ((silicon adj carbide) or sic) and (\$4crystalline with (order adj ratio))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/03 13:11
-	8	(cvd or (chemical adj vapor)) and ((silicon adj carbide) or sic) and (order adj ratio)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/03 13:12
-	4	((cvd or (chemical adj vapor)) and ((silicon adj carbide) or sic) same (conductivity with (kw or w or mk or "w/mk" or "kw/mk"))) and (stacking adj fault)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/03 13:14
-	4	((cvd or (chemical adj vapor)) and ((silicon adj carbide) or sic) same (conductivity with (kw or w or mk or "w/mk" or "kw/mk"))) and (stack\$3 adj fault)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/03 13:14
-	62	(cvd or (chemical adj vapor)) same ((silicon adj carbide) or sic) same (conductivity with (kw or w or mk or "w/mk" or "kw/mk"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/03 13:46
-	13	((cvd or (chemical adj vapor)) same ((silicon adj carbide) or sic) same (conductivity with (kw or w or mk or "w/mk" or "kw/mk"))) and (defect or fault)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/03 13:15
-	3	((cvd or (chemical adj vapor)) same ((silicon adj carbide) or sic) same (conductivity with (kw or w or mk or "w/mk" or "kw/mk"))) and fault	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/03 13:16
-	16	((cvd or (chemical adj vapor)) same ((silicon adj carbide) or sic) same (conductivity with (kw or w or mk or "w/mk" or "kw/mk"))) and stack\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/03 13:16
-	4	((cvd or (chemical adj vapor)) and ((silicon adj carbide) or sic) same (conductivity with (kw or w or mk or "w/mk" or "kw/mk"))) and (stack\$3 with fault\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/03 13:17
-	10	((cvd or (chemical adj vapor)) same ((silicon adj carbide) or sic) same (conductivity with (kw or w or mk or "w/mk" or "kw/mk"))) and mandrel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/03 13:47
-	2217297	((cvd or (chemical adj vapor)) same ((silicon adj carbide) or sic) same (conductivity with (kw or w or mk or "w/mk" or "kw/mk"))) and mandrel) parallel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/03 13:47
-	1	((cvd or (chemical adj vapor)) same ((silicon adj carbide) or sic) same (conductivity with (kw or w or mk or "w/mk" or "kw/mk"))) and mandrel) and parallel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/03 13:47